

High Voltage NPN Silicon Power Transistors

TIP47G, TIP48G, TIP50G

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

Features

- Popular TO–220 Plastic Package
- Complementary to the MJE5730 and MJE5731 Series
- These Devices are Pb-Free and are RoHS Compliant*

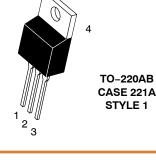
MAXIMUM RATINGS

Symbol	Rating	TIP47	TIP48	TIP50	Unit		
V _{CEO}	Collector - Emitter Voltage	250	300	400	Vdc		
V _{CB}	Collector - Base Voltage 350 400 500						
V _{EB}	Emitter - Base Voltage	5.0			Vdc		
I _C	Collector Current - Continuous		1.0		Adc		
I _{CM}	Collector Current - Peak		2.0				
I _B	Base Current 0.6				Adc		
P _D	Total Power Dissipation @ T _C = 25°C Derate above 25°C	40 0.32			W W/°C		
P _D	Total Power Dissipation @ T _C = 25°C Derate above 25°C	2.0 0.016		W W/°C			
E	Unclamped Inducting Load Energy (See Figure 8)	20		mJ			
T _J , T _{stg}	Operating and Storage -65 to +150 Junction Temperature Range				°C		

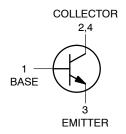
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

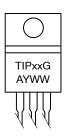
Symbol	Characteristic	Max	Unit
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	3.125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W



1.0 AMPERE POWER TRANSISTORS NPN SILICON 250-300-400 VOLTS 40 WATTS



MARKINGDIAGRAM



TIPxx = Device Code xx = 47, 48, or 50 A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, <u>SOLDERRM/D</u>.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Characteristic		Min	Max	Unit
FF CHARAC	TERISTICS			•	
V _{CEO(sus)}	Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 30 \text{ mAdc}, I_B = 0)$	TIP47 TIP48 TIP50	250 300 400	- - -	Vdc
I _{CEO}	Collector Cutoff Current $ \begin{aligned} &(V_{CE}=150 \text{ Vdc}, \text{ I}_{B}=0) \\ &(V_{CE}=200 \text{ Vdc}, \text{ I}_{B}=0) \\ &(V_{CE}=300 \text{ Vdc}, \text{ I}_{B}=0) \end{aligned} $	TIP47 TIP48 TIP50	- - -	1.0 1.0 1.0	mAdc
I _{CES}	Collector Cutoff Current $ \begin{aligned} &(V_{CE}=350 \text{ Vdc}, V_{BE}=0) \\ &(V_{CE}=400 \text{ Vdc}, V_{BE}=0) \\ &(V_{CE}=500 \text{ Vdc}, V_{BE}=0) \end{aligned} $	TIP47 TIP48 TIP50	- - -	1.0 1.0 1.0	mAdc
I _{EBO}	Emitter Cutoff Current $(V_{BE} = 5.0 \text{ Vdc}, I_C = 0)$		-	1.0	mAdc
N CHARACT	ERISTICS (Note 1)				
h _{FE}	DC Current Gain $ \begin{aligned} &(I_C=0.3 \text{ Adc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=1.0 \text{ Adc, } V_{CE}=10 \text{ Vdc)} \end{aligned} $		30 10	150 –	-
V _{CE(sat)}	Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.2 Adc)		-	1.0	Vdc
V _{BE(on)}	Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)		-	1.5	Vdc
YNAMIC CHA	ARACTERISTICS			•	
f _T	Current–Gain – Bandwidth Product ($I_C = 0.1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 2.0 \text{ MHz}$)		10	-	MHz
h _{fe}	Small-Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		25	-	_

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width $\leq 300 \ \mu s$, Duty Cycle $\leq 2.0\%$.

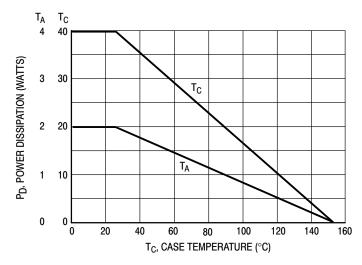


Figure 1. Power Derating

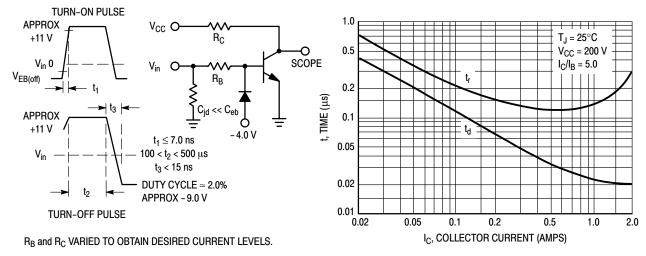


Figure 2. Switching Time Equivalent Circuit

Figure 3. Turn-On Time

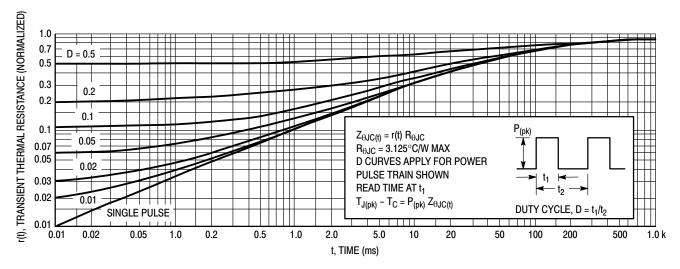


Figure 4. Thermal Response

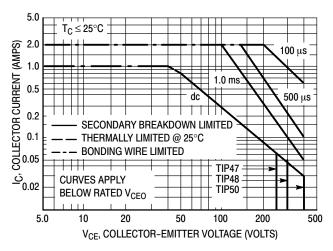


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

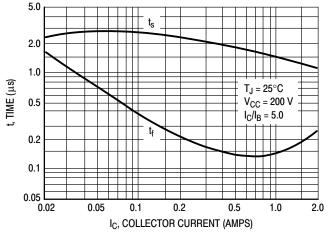


Figure 6. Turn-Off Time

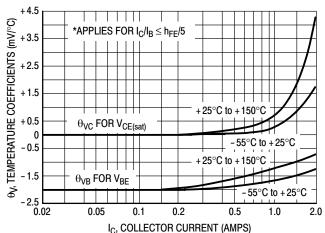
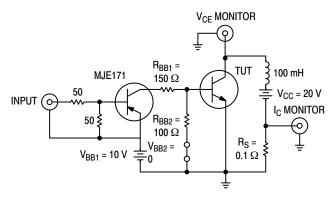


Figure 7. Temperature Coefficients



Note A: Input pulse width is increased until $I_{CM} = 0.63$ A.

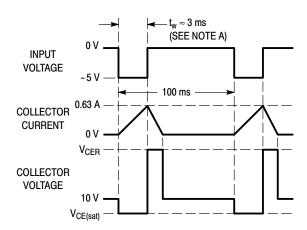


Figure 8. Inductive Load Switching

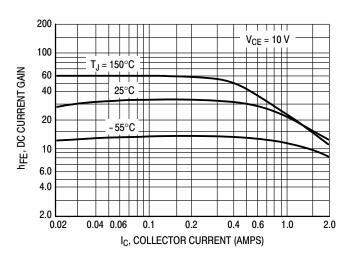


Figure 9. DC Current Gain

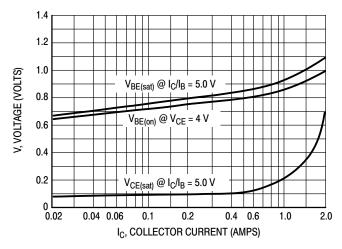
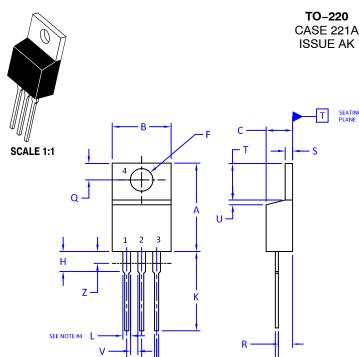


Figure 10. "On" Voltages

ORDERING INFORMATION

Device	Package	Shipping
TIP47G	TO-220 (Pb-Free)	50 Units / Rail
TIP48G	TO-220 (Pb-Free)	50 Units / Rail
TIP49G	TO-220 (Pb-Free)	50 Units / Rail
TIP50G	TO-220 (Pb-Free)	50 Units / Rail





CASE 221A

DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	BASE COLLECTOR EMITTER COLLECTOR	STYLE 2: PIN 1. 2. 3. 4.		STYLE 3: PIN 1. 2. 3. 4.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	GATE DRAIN SOURCE DRAIN	STYLE 6: PIN 1. 2. 3. 4.	ANODE CATHODE ANODE CATHODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.	GATE COLLECTOR EMITTER COLLECTOR	STYLE 10: PIN 1. 2. 3. 4.	GATE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2

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